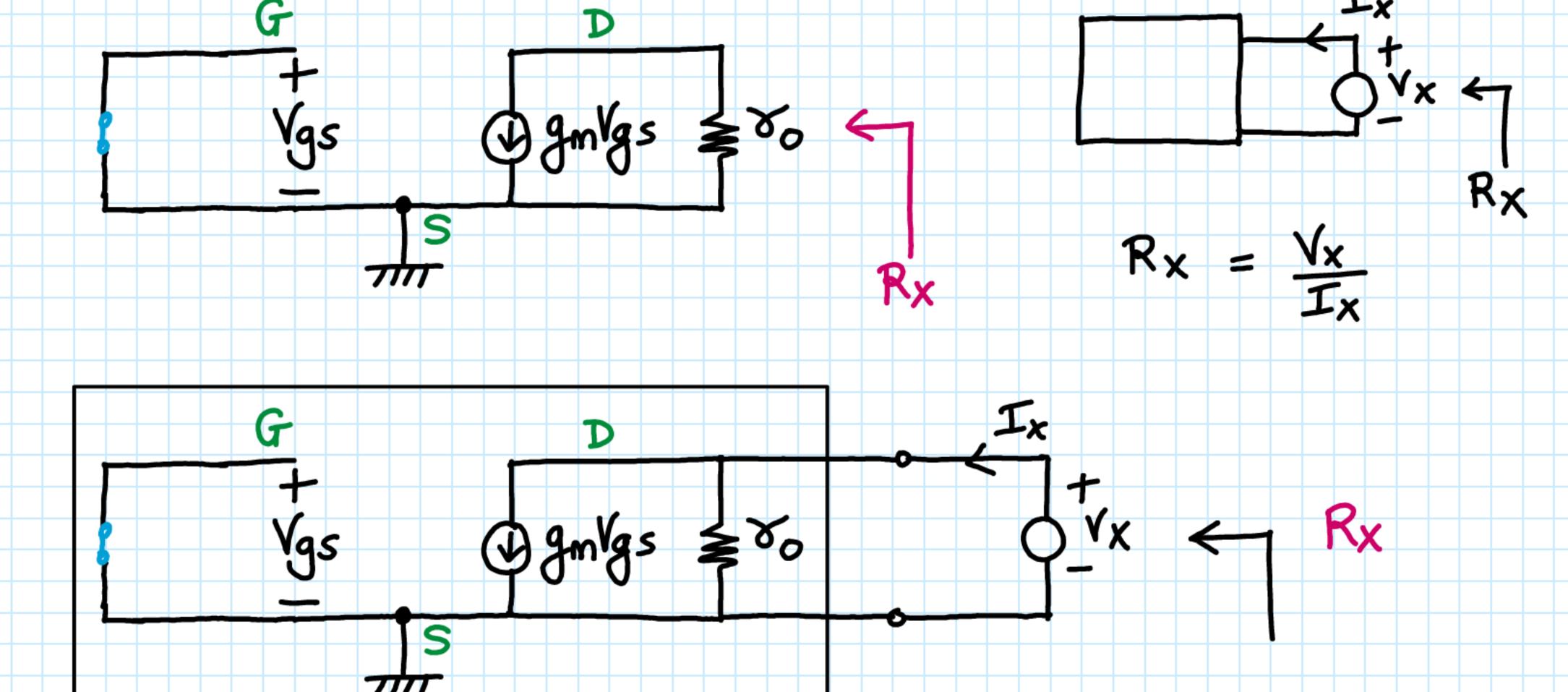


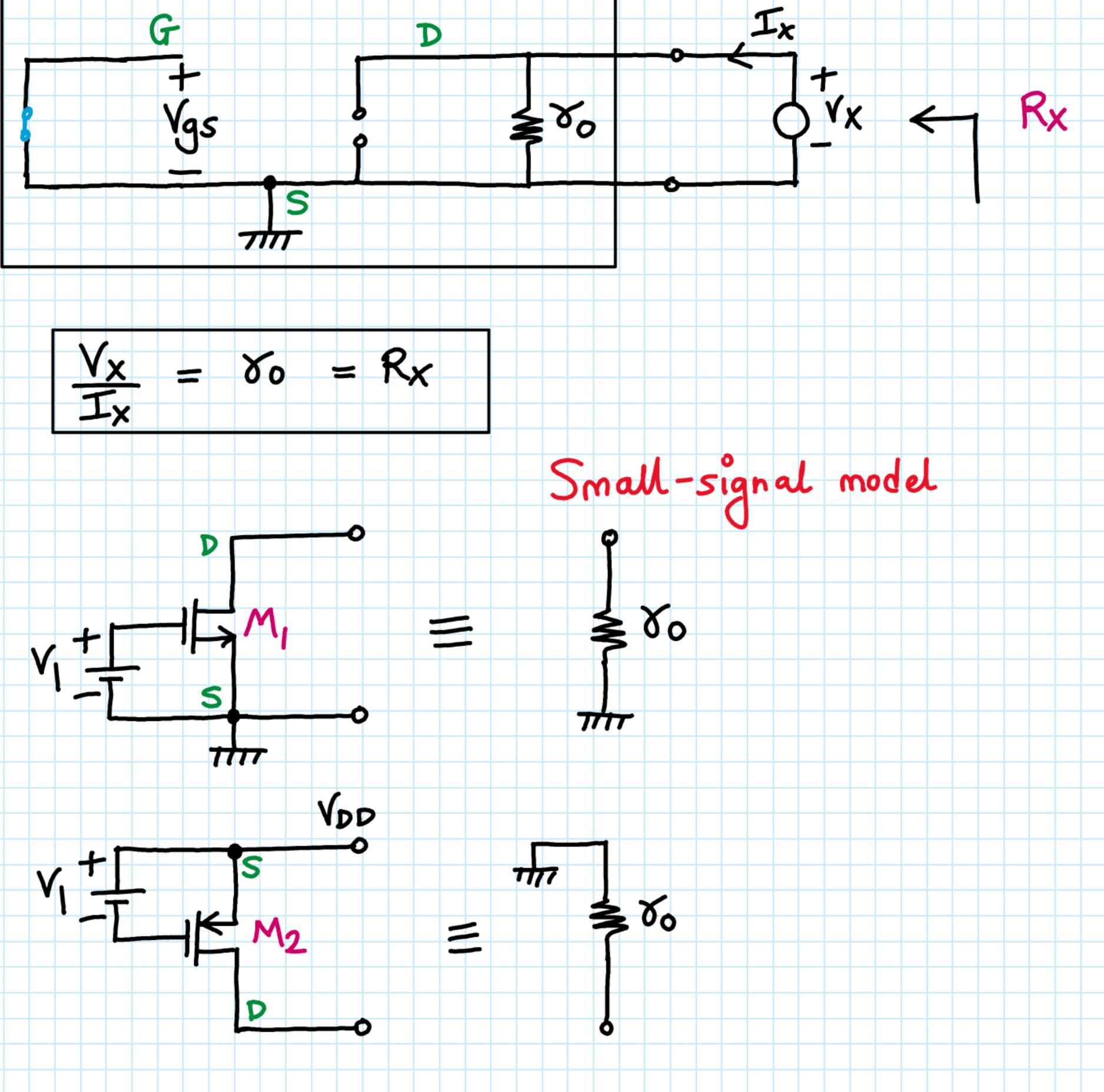
Current flows into the node

Bias voltage such that M2 in saturation

3) Small-signal Model: for (a) Calculate port impedance:

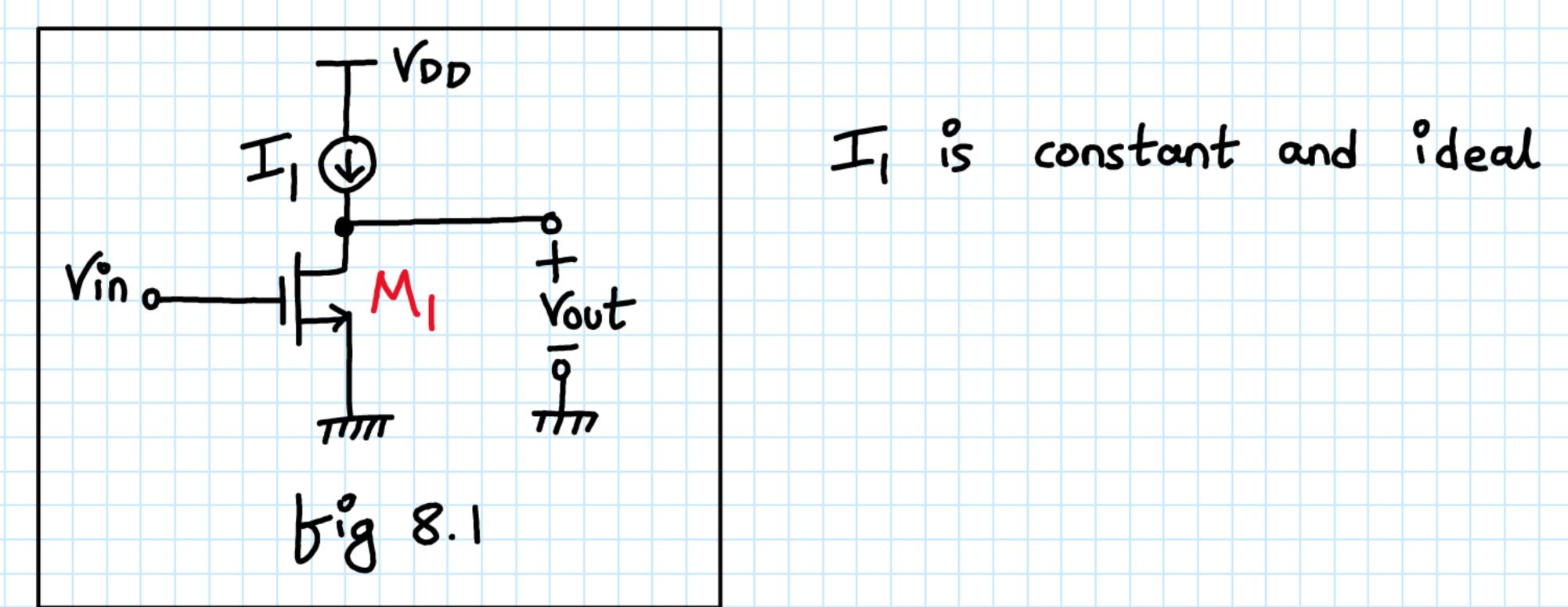


 $Vgs = 0 \rightarrow gmVgs = 0$ i.e gmVgs couvert souvere become reduntant île Circuit reduces to



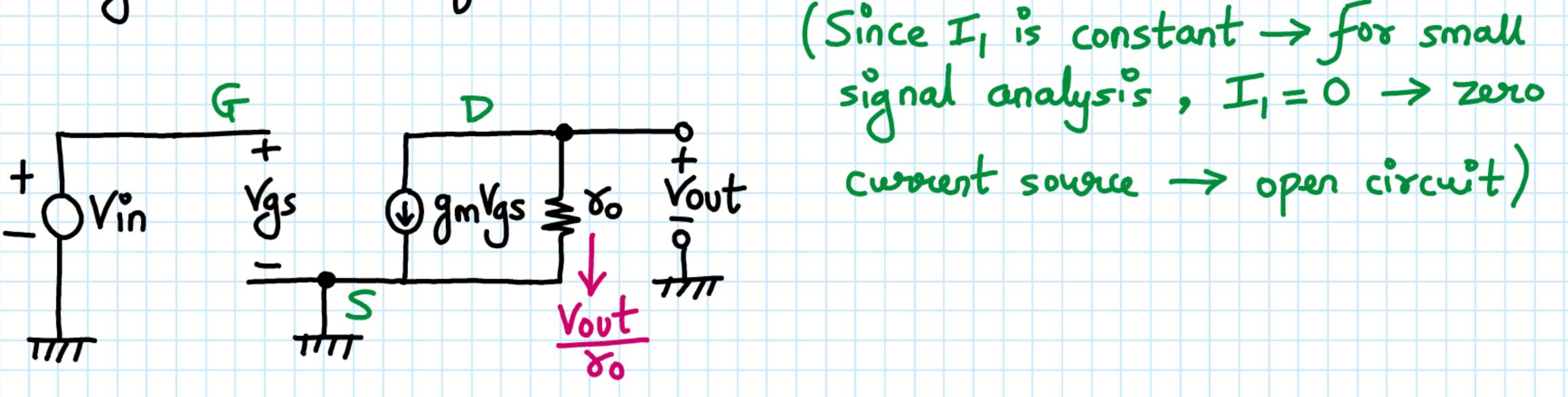
(4) Key points: Any time we see a MOSFET operating as a constant current source, we can for our small signal purpose's -> can replace it with a single resistance equal to vo

Q1. Assuming that M1 in fig 8.1 is biased in saturation, calculate the small signal voltage gain of the circuit



Solution:

1) Small signal model of circuit



2) Vin = Ygs

(3) KCL at D' node gives,

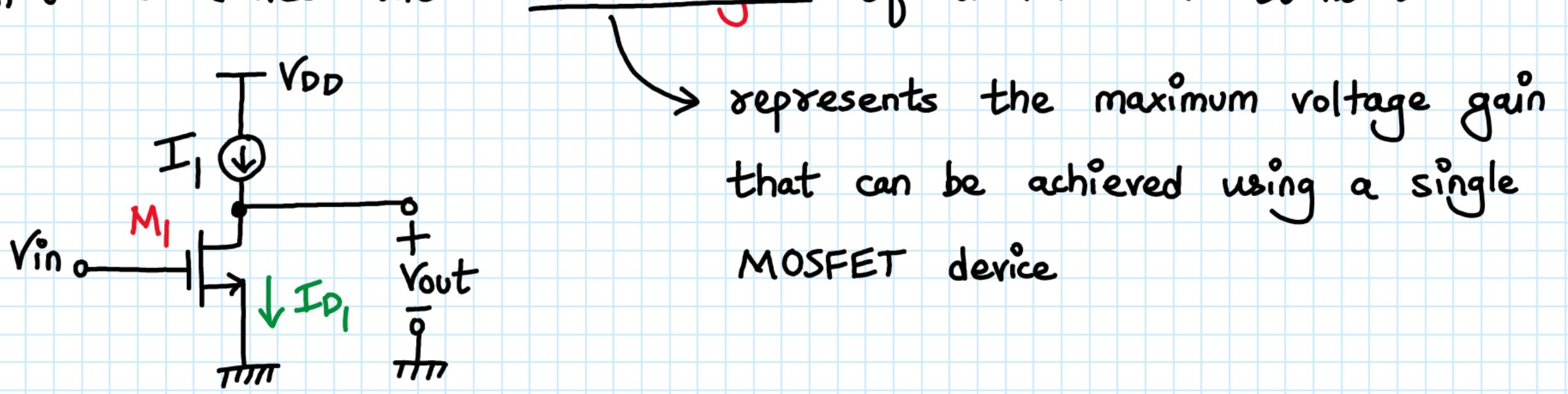
$$\hat{l} \cdot e = -g_m \delta_0 \dots (1.1)$$

I, is a current source and ideally has an infinite impedance

··· Small -signal voltage gain

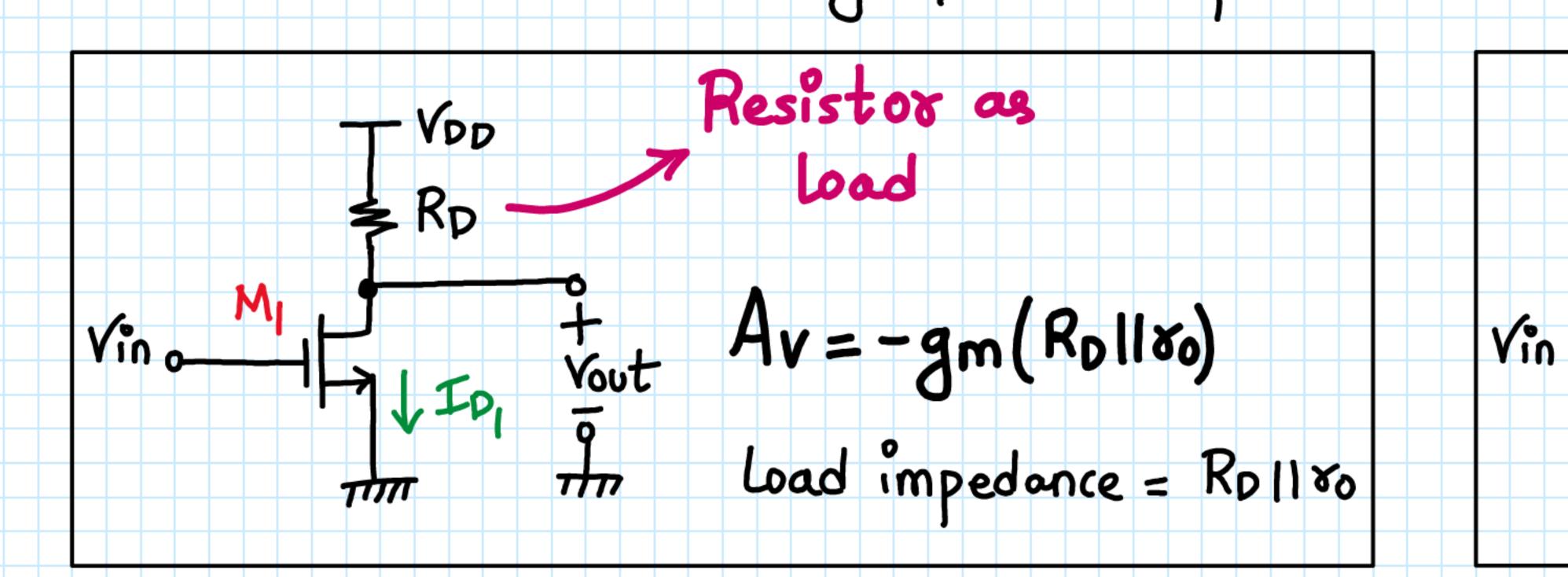
4) Av = -gmro is the maximum gain of this amplifier

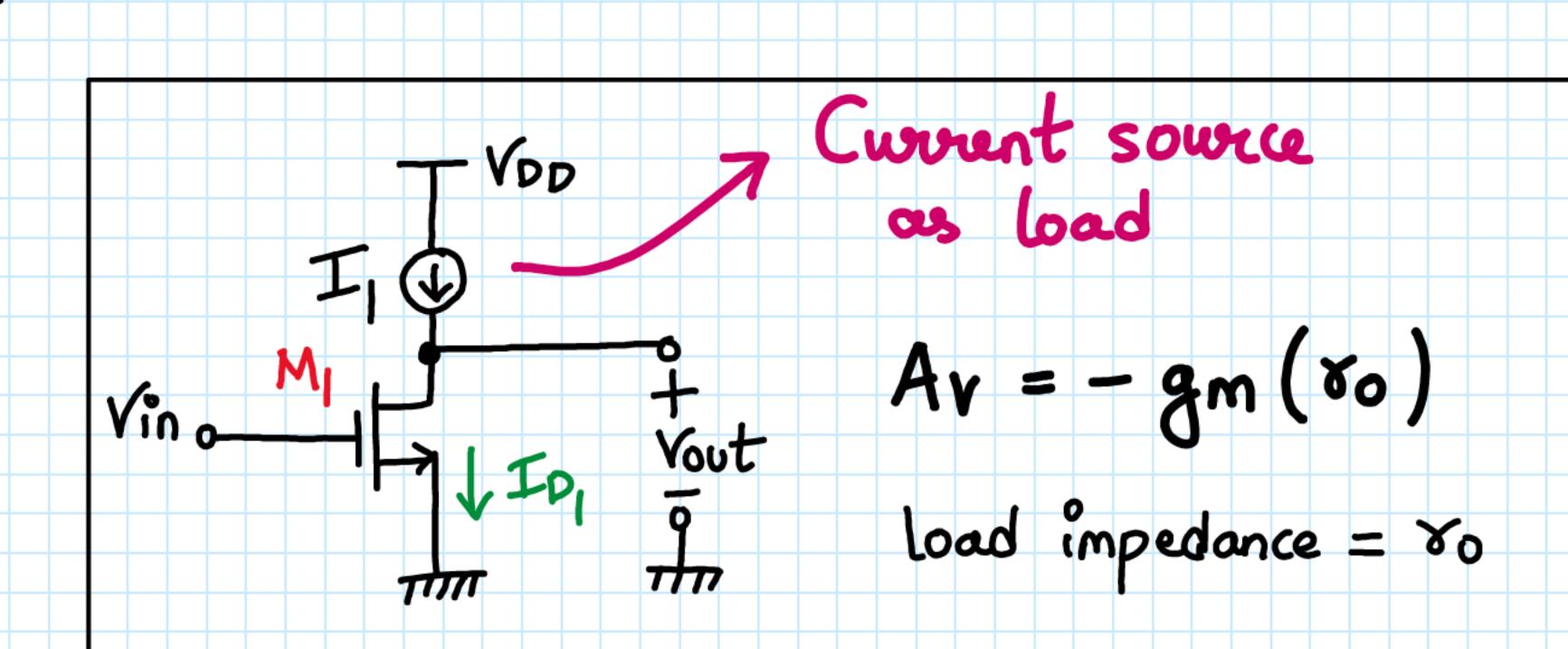
(5) "gm 80" is called the "intrinsic gain" of a MOSFET transistor



6 Important Conclusion: To maximize the voltage gain Av -> we must

maximize the (small-signal) load impedance





7) How can Vin change if I, is constant? $ID_{1} = \frac{1}{2} \mu_{1} Cox \frac{W}{L} (V_{GS} - V_{th})^{2} (1 + 2V_{DS})$ VGS = Yin and YDS = Yout = 1 m Cox W (Vin - Vth) (1+ 2 Vout) = I,

-> From equation (1.2), as Vin changes, Vout also changes to keep II constant